



AO4850

Dual N-Channel Enhancement Mode Field Effect Transistor

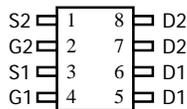


General Description

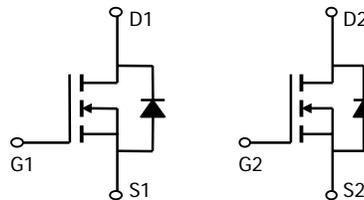
The AO4850 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The two MOSFETs may be used in H-bridge, Inverters and other applications. AO4850 is Pb-free (meets ROHS & Sony 259 specifications).

Features

V_{DS} (V) = 75V
 I_D = 3.1A (V_{GS} = 10V)
 $R_{DS(ON)}$ < 130m Ω (V_{GS} = 10V)
 $R_{DS(ON)}$ < 165m Ω (V_{GS} = 4.5V)



SOIC-8



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum		Units	
		10 Sec	Steady State		
Drain-Source Voltage	V_{DS}	75		V	
Gate-Source Voltage	V_{GS}	± 25		V	
Continuous Drain Current ^A	I_D	$T_A=25^\circ\text{C}$	3.1	2.3	A
		$T_A=70^\circ\text{C}$	2.4	1.8	
Pulsed Drain Current ^B	I_{DM}	15			
Power Dissipation	P_D	$T_A=25^\circ\text{C}$	2	1.1	W
		$T_A=70^\circ\text{C}$	1.3	0.7	
Avalanche Current ^B	I_{AR}	10		A	
Repetitive avalanche energy 0.3mH ^B	E_{AR}	15		mJ	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		$^\circ\text{C}$	

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A $t \leq 10\text{s}$	$R_{\theta JA}$	50	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A Steady-State		82	110	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C Steady-State	$R_{\theta JL}$	41	50	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=10\text{mA}$, $V_{GS}=0\text{V}$	75			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=75\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 25\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1	2.3	3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$, $V_{DS}=5\text{V}$	15			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=3.1\text{A}$ $T_J=125^\circ\text{C}$		105	130	m Ω
		$V_{GS}=4.5\text{V}$, $I_D=2\text{A}$		126	165	
		$V_{GS}=10\text{V}$, $I_D=3.1\text{A}$				
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=3.1\text{A}$		10		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.77	1	V
I_S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=30\text{V}$, $f=1\text{MHz}$		290	380	pF
C_{oss}	Output Capacitance			54		pF
C_{rss}	Reverse Transfer Capacitance			24		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		2.4	3.5	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=30\text{V}$, $I_D=3.1\text{A}$		5.14	7	nC
$Q_g(4.5\text{V})$	Total Gate Charge			2.34		nC
Q_{gs}	Gate Source Charge			0.97		nC
Q_{gd}	Gate Drain Charge			1.18		nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=10\text{V}$, $V_{DS}=30\text{V}$, $R_L=9.7\Omega$, $R_{GEN}=3\Omega$		4		ns
t_r	Turn-On Rise Time			3.4		ns
$t_{D(off)}$	Turn-Off Delay Time			14.4		ns
t_f	Turn-Off Fall Time			2.4		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=3.1\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		30.2	45	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=3.1\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		21.5		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6 are obtained using $<300 \mu\text{s}$ pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

Rev 1: May. 2007

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

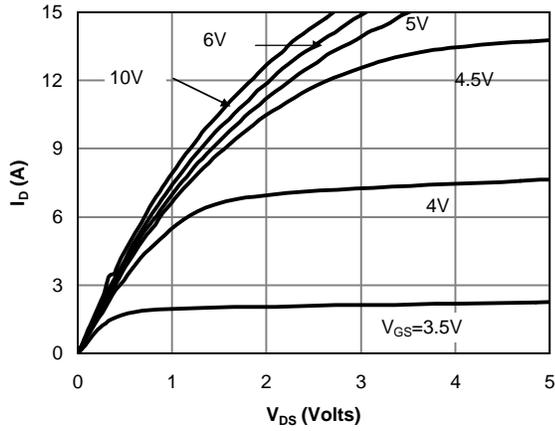


Fig 1: On-Region Characteristics

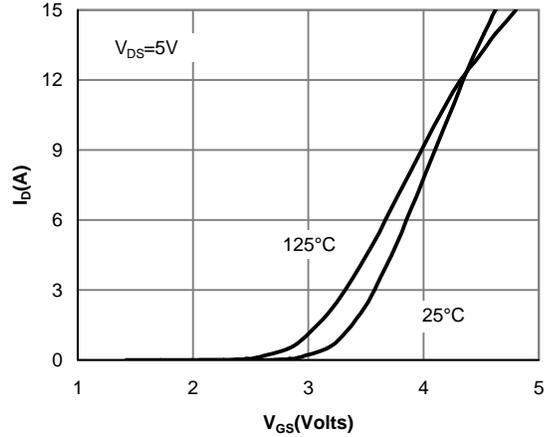


Figure 2: Transfer Characteristics

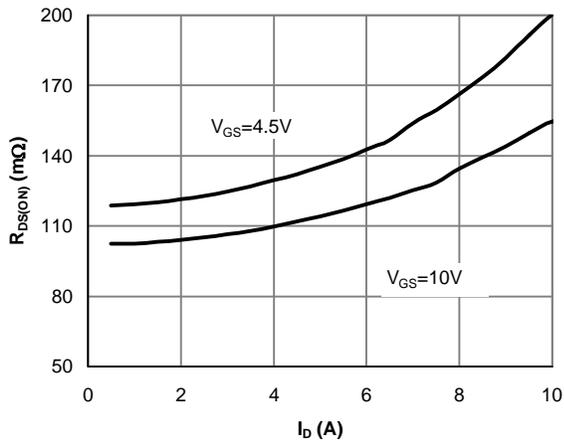


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

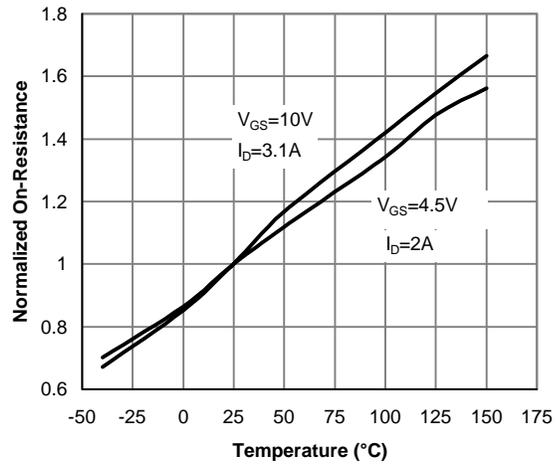


Figure 4: On-Resistance vs. Junction Temperature

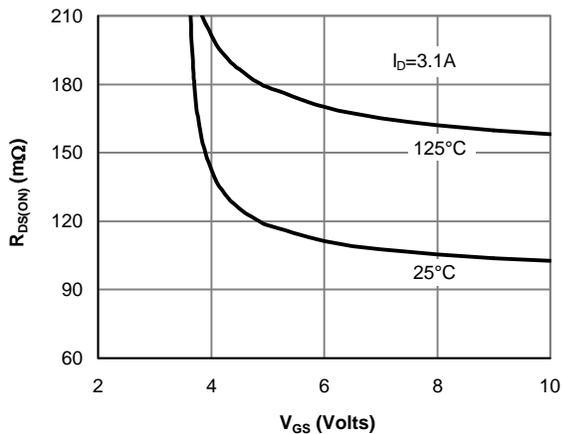


Figure 5: On-Resistance vs. Gate-Source Voltage

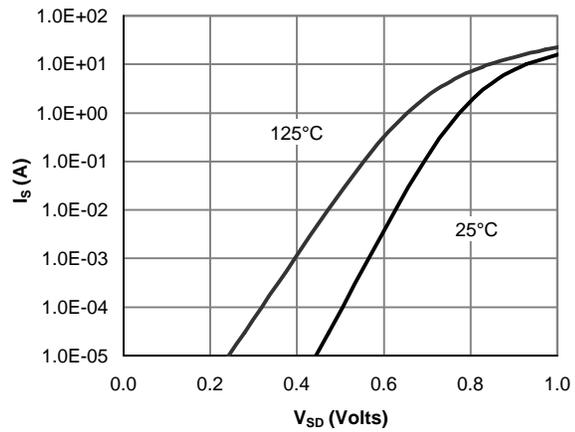


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

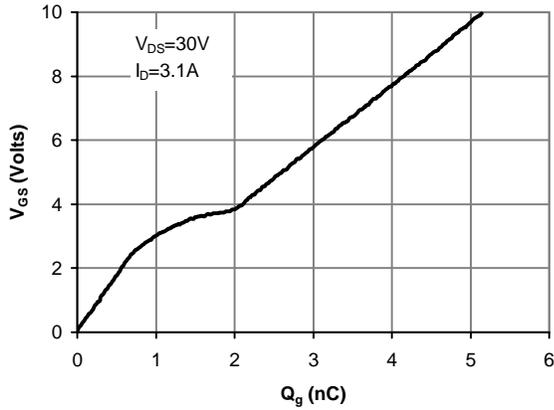


Figure 7: Gate-Charge Characteristics

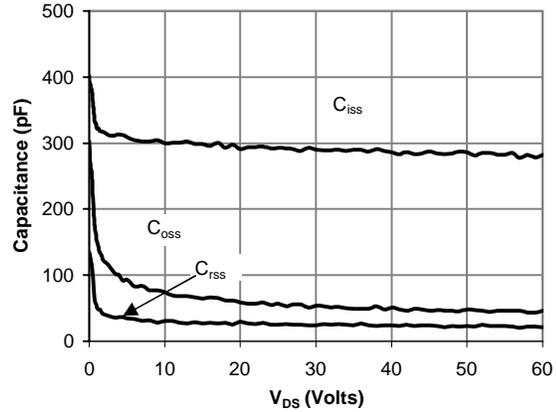


Figure 8: Capacitance Characteristics

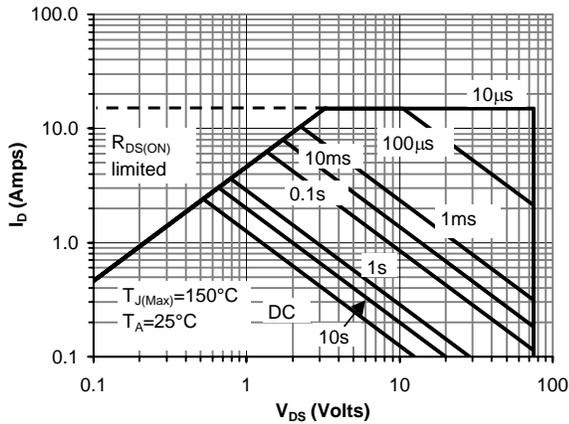


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

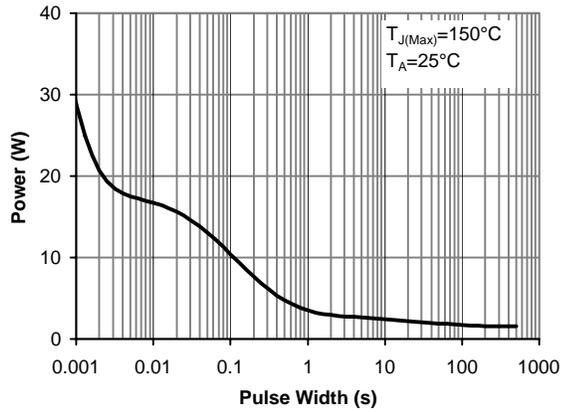


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

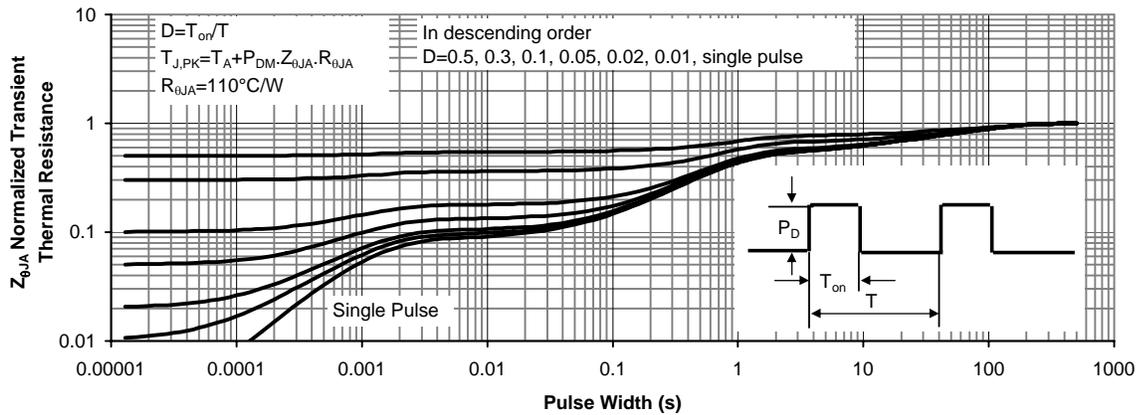


Figure 11: Normalized Maximum Transient Thermal Impedance